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(71) Applicant (for all designated States except US): OTICON A/S [DK/DK]; Strandvejen 58, DK-2900 Hellerup (DK).

(72) Inventors; and

(75) Inventors/Applicants (for US only): RASMUSSEN,

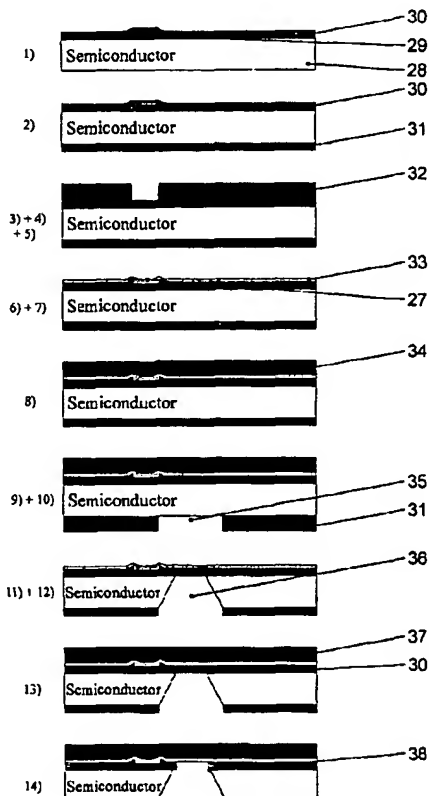
Frank, Engel [DK/DK]; Co Oticon A/S, Strandvejen 58, DK-2900 Hellerup (DK). SKINDHOJ, Jorgen [DK/DK]; c/o Oticon A/S, Strandvejen 58, DK-2900 Hellerup (DK). PETERSEN, Anders, Erik [DK/DK]; c/o Oticon A/S, Strandvejen 58, DK-2900 Hellerup (DK).

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(54) Title: FEED-THROUGH PROCESS AND AMPLIFIER WITH FEED-THROUGH



(57) Abstract: The invention concerns a process for generating a feed-through in a semiconductor wafer, which has electric circuitry embedded in a front surface whereby the hole for the feed-through is generated by the combined use of a front side protection layer and a wet KOH etch process etching the hole from the back side of the wafer, where a photomasking process is subsequently used to define the via followed by deposition of the via material.

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